

EL - 23G

The EL - 23G, a high - power GaAs IRED mounted in a clear sidelooking package, is compact, low profile, and easy to mount.

FEATURES

- Compact
- Low profile package
- Low - cost
- Sidelooking plastic package

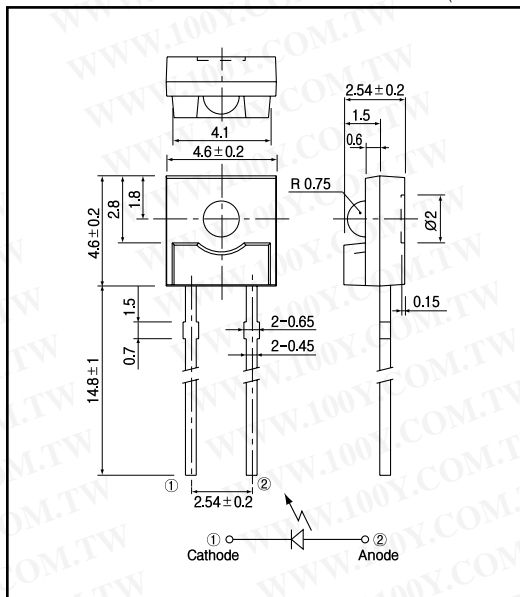
APPLICATIONS

- Photointerrupters
- Optical switches
- Toys

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25)

Item	Symbol	Rating	Unit
Reverse voltage	V _R	5	V
Forward current	I _F	60	mA
Pulse forward current ¹	I _{FP}	1	A
Power dissipation	P ₀	100	mW
Operating temp.	T _{opr.}	- 20 - + 100	
Storage temp.	T _{stg.}	- 30 ~ + 100	
Soldering temp. ²	T _{sol.}	240	

¹1. pulse width : tw 100 ꝑec.period : T=10msec.

²2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

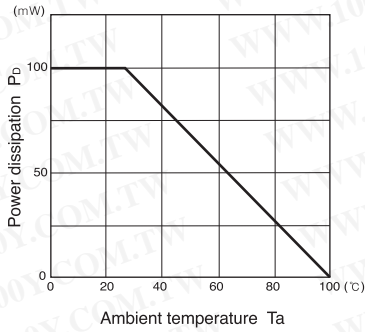
(Ta=25)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V _F	I _F =60mA		1.3	1.6	V
Reverse current	I _R	V _R =5V			10	µA
Capacitance	C _t	f=1MHz		25		pF
Radiant intensity	P ₀	I _F =60mA		2.0		mW/sr
Peak emission wavelength	ꝑ	I _F =60mA		940		nm
Spectral bandwidth 50%		I _F =60mA		50		nm
Half angle				± 30		deg.

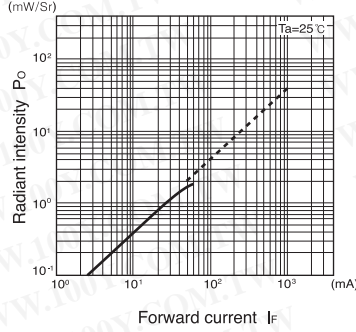
Infrared Emitting Diodes(GaAs)

EL - 23G

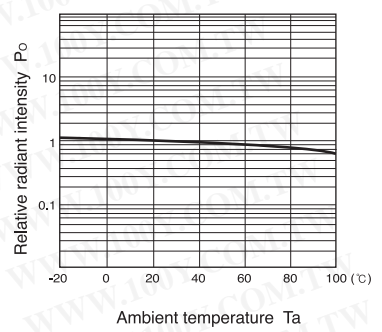
Power dissipation Vs. Ambient temperature



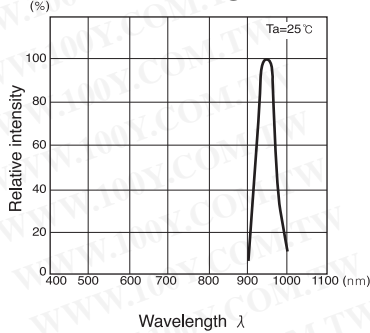
Radiant intensity Vs. Forward current



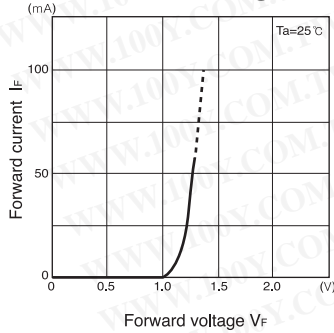
Relative radiant intensity Vs. Ambient temperature



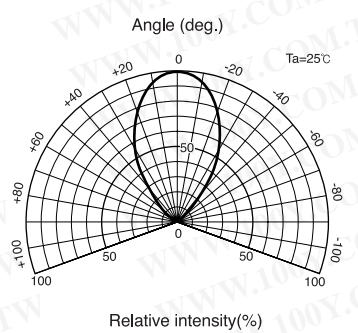
Relative intensity Vs. Wavelength



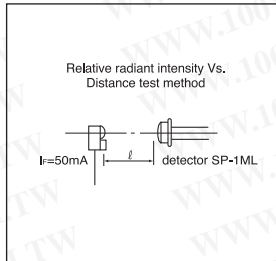
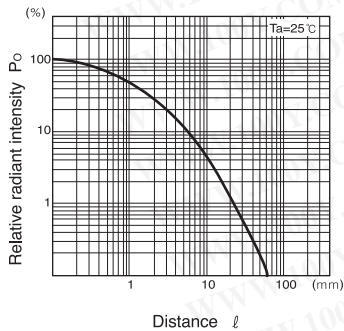
Forward current vs. Forward voltage



Radiant Pattern



Relative radiant intensity Vs. Distance



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